

**REMARKS**

Applicants note with appreciation the Examiners allowance of claims 1-5, 7-9, 11-14 and 20-22. Applicants, however, submit the following comments regarding the Examiner's Reasons for Allowance stated on Page 3 of the Notice of Allowance. In the Reasons for Allowance, the Examiner indicated that none of the references of record teach or suggest "a method of forming a fin for a FinFET comprising...forming a fin in a trench, a spacer on an upper surface of the fin, a liner on the spacer and fin, and removing the liner." This statement of reasons for allowance appears to be directed to the features of claim 1. Applicants note, however, that independent claim 20 recites a combination of features not suggested or disclosed by the references of record. For example, claim 20 recites the following combination of features: "a method of forming a fin for a fin field effect transistor (FinFET), comprising: defining a trench in a layer of first material; growing a second material in the trench to form the fin; removing the layer of first material; forming a liner on the fin, the liner comprising a third material; and removing the liner to leave the fin." Applicants submit that it is the novel and non-obvious combination of features recited in both claims 1 and 20 that distinguish these claims over the references of record.

U.S. Patent Application No. 10/633,499  
Attorney's Docket No. H1134

To the extent necessary, a petition for an extension of time under 37 CFR § 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 50-1070 and please credit any excess fees to such deposit account.

Respectfully submitted,

By:  (Glenn Snyder  
Reg. No. 41,428)  
Tony M. Cole  
 Registration No. 43,417

Date: October 29, 2004

Harrity & Snyder, L.L.P.  
11240 Waples Mill Road  
Suite 300  
Fairfax, Virginia 22030  
Main: (571) 432-0800  
Direct: (386) 575-2713

Customer Number: **45114**